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**SIDDHARTH INSTITUTE OF ENGINEERING & TECHNOLOGY:: PUTTUR**  
(AUTONOMOUS)  
**BTECH I Year I Semester Supplementary Examinations November-2021**  
**APPLIED PHYSICS**

[Common to CSE, CSE (AI & ML), CSE (IOT) & CSIT]

Time: 3 hours

Max. Marks: 60

(Answer all Five Units 5 x 12 = 60 Marks)

**UNIT-I**

- 1 a Describe the formation of Newton's ring with necessary theory with relevant diagram and derive the expressions for dark and bright fringes. **L3 9M**  
b In a Newton's rings experiment, the diameter of the 5<sup>th</sup> ring is 0.30 cm and the diameter of the 15<sup>th</sup> ring is 0.62 cm. Calculate the diameter of the 25<sup>th</sup> ring. **L4 3M**

**OR**

- 2 a Explain the theory of Fraunhofer diffraction due to single slit. **L4 8M**  
b Obtain conditions for bright and dark fringes in single slit diffraction pattern and draw intensity distribution. **L4 4M**

**UNIT-II**

- 3 a Describe the electrical conductivity in a metal using quantum free electronic theory. **L3 8M**  
b Write advantages of quantum free electron theory over classical free electron theory. **L1 4M**

**OR**

- 4 a State and Explain Gauss's theorem for divergence and Stoke's theorem for curl. **L4 12 M**

**UNIT-III**

- 5 a Describe the construction and working principle of Nd: YAG laser with the help of a neat diagram. **L3 9M**  
b Calculate the wavelength of emitted radiation from GaAs laser which has a band gap of 1.44eV. **L4 3M**

**OR**

- 6 a Describe optical fiber communication system with block diagram. **L3 8M**  
b Mention the application of optical fiber in sensors. **L1 4M**

**UNIT-IV**

- 7 a What is intrinsic semiconductor and explain the formation of extrinsic semiconductors through doping? **L1 8 M**  
b The following data are given for an intrinsic Ge at 300K. Calculate the conductivity of the sample? ( $n_i = 2.4 \times 10^{19} \text{m}^{-3}$ ,  $\mu_e = 0.39 \text{m}^2 \cdot \text{V}^{-1} \text{S}^{-1}$ ,  $\mu_p = 0.19 \text{m}^2 \cdot \text{V}^{-1} \text{S}^{-1}$ ). **L4 4 M**

**OR**

- 8 a Explain the formation of p-n junction. **L4 4M**  
b Describe the construction and working mechanism of Photodiode. **L3 8M**

**UNIT-V**

- 9 a Explain Josephson effect in superconductors. **L4 8M**  
b Write the applications of superconductors. **L1 4M**

**OR**

- 10 a Explain why surface area to volume ratio very large for nano materials? **L4 7M**  
b Write the mechanical, magnetic and optical properties of nanomaterials. **L1 5M**

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